Descriptions

This 100V, 68A N-Channel MOSFET in a TO-252 Plastic Package.

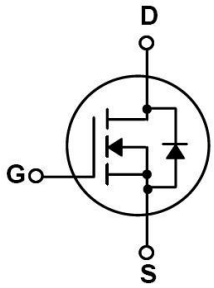
Features

- Low RDS(on)
- Low gate charge
- Low C_{rss}
- Fast switching
- HF Product.

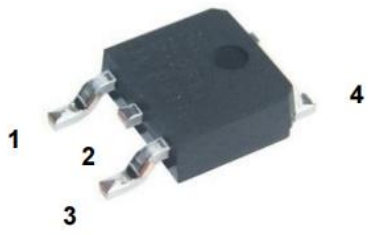
Applications

- Suited for low voltage applications such as automotive.
- DC/DC Converters
- and high efficiency switching for power management in portable and battery operated products
- Meet the stringent requirements of automotive applications

Equivalent Circuit



Pinning



PIN1: G PIN 2: D PIN 3: S PIN 4: D

Absolute Maximum Ratings(Ta=25℃)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Drain Current - Continuous		I_D	68	A
Drain Current – Pulsed		I_{DM}	156	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		$P_D(T_c=25℃)$	75	W
Single Pulse Avalanche Energy(L=0.5mH)		E_{AS}	119	mJ
Avalanche Current(L=0.5mH)		I_{AS}	18.5	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	℃
Thermal resistance, junction - ambient	t ≤ 10s	$R_{\theta JA}$	20	℃/ W
	Steady-State		50	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	1.7	

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	109		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V V_{GS}=0V			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250μA	2	2.9	4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=30A		7	8	mΩ
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=1A			1.2	V
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V, f=1MHz		3.1		Ω
Input Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1.0MHz		2500		pF
Output Capacitance	C_{oss}			1250		
Reverse Transfer Capacitance	C_{rss}			110		
Total Gate Charge	Q_g	V_{GS}=10V, V_{DS}=50V, I_D=20A		25		nC
Gate Source Charge	Q_{gs}			6		
Gate Drain Charge	Q_{gd}			3.5		

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V V_{DS}=50V R_L=2.5 R_{GEN}=3Ω		8.5		ns
Turn-On Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			23		
Turn-Off Fall Time	t_f			3.5		

Electrical Characteristic Curve

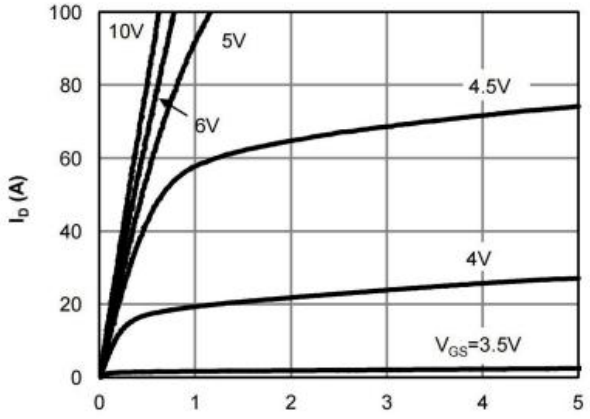


Fig 1: On-Region Characteristics

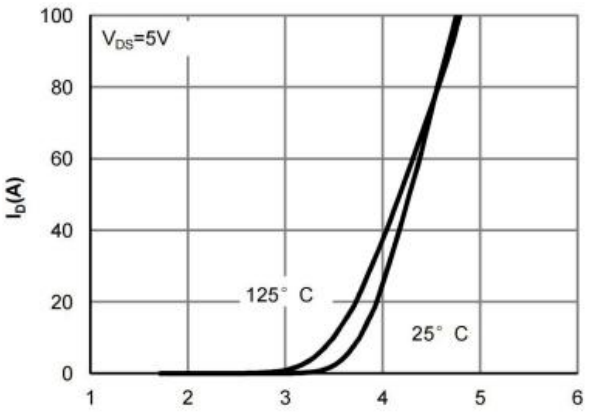


Figure 2: Transfer Characteristics

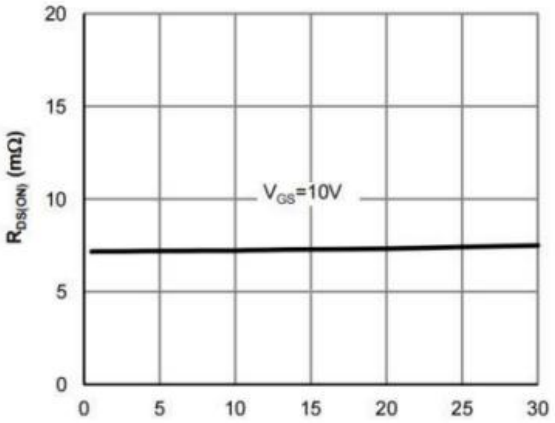


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

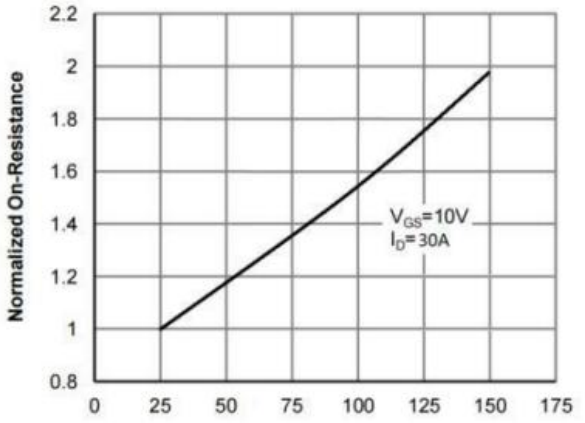


Figure 4: On-Resistance vs. Junction Temperature

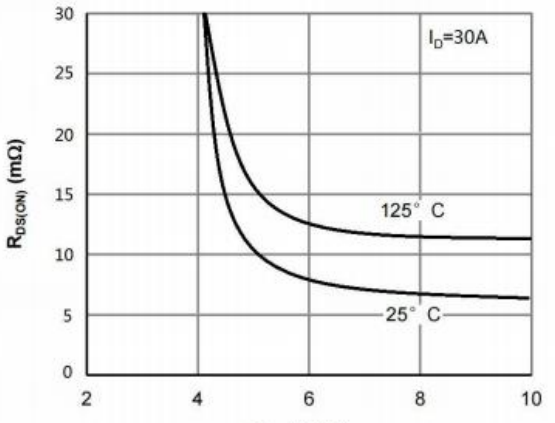


Figure 5: On-Resistance vs. Gate-Source Voltage

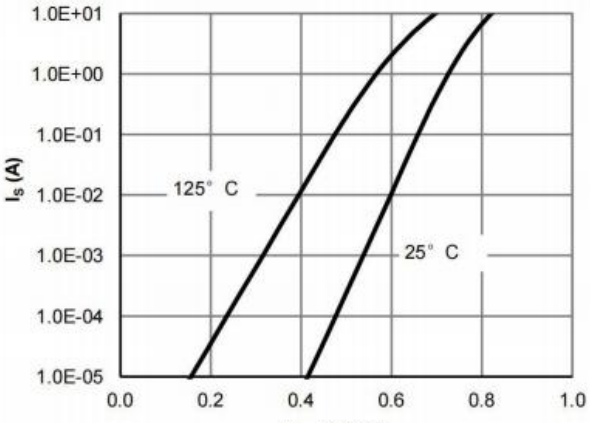


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

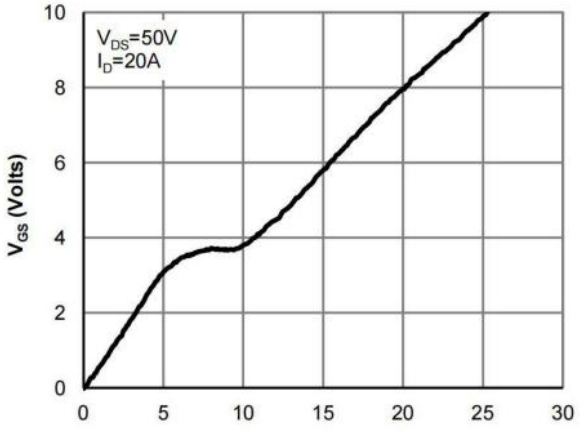


Figure 7: Gate-Charge Characteristics

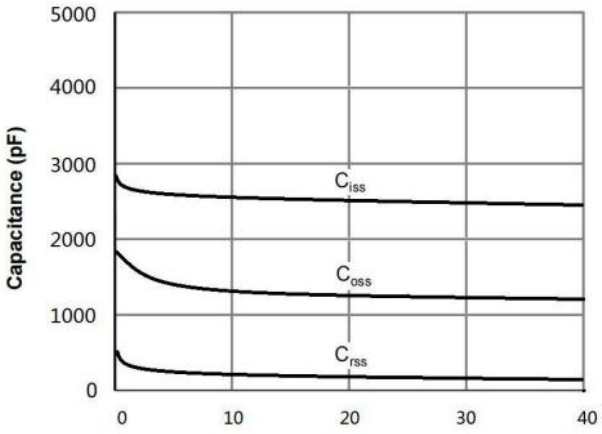


Figure 8: Capacitance Characteristics

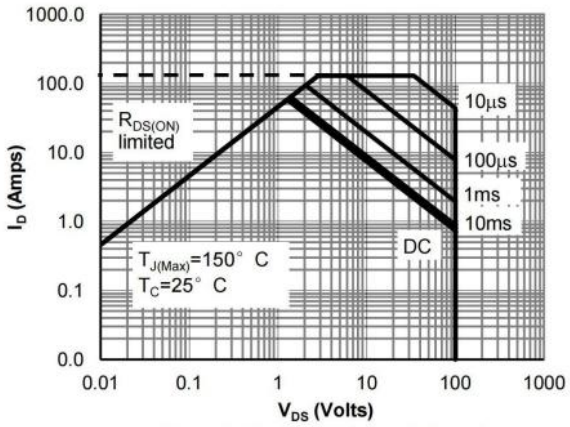


Figure 9: Maximum Forward Biased Safe Operating Area

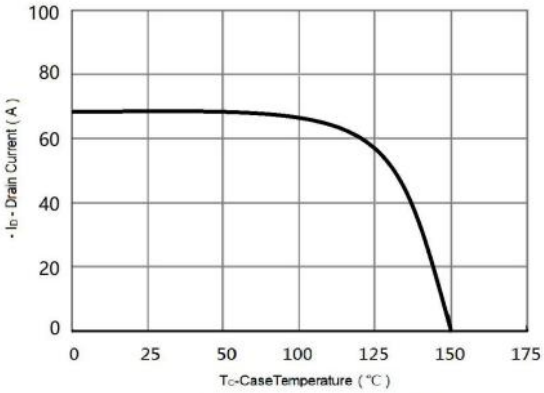


Figure10. Maximum Continuous Drain Current Vs Case Temperature

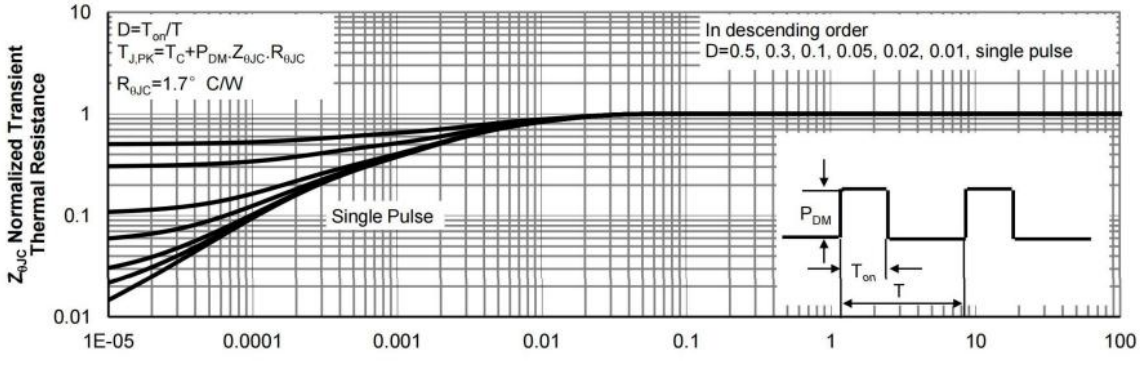


Figure 11: Normalized Maximum Transient Thermal Impedance

Marking Instructions

Note:

COT: Company Logo

080N10SH: Product Type.

****: Lot No. Code, code change with Lot No.

Packaging SPEC

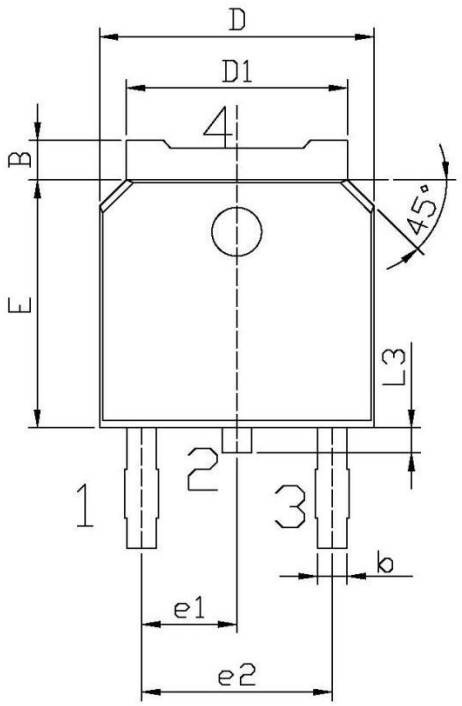
REEL INFORMATION

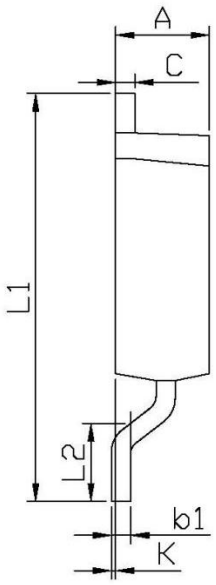
Package Type	Units					Dimension (unit：mm³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	6	30,000	13″ ×16	360×360×50	380×335×366

TUBE INFORMATION

Package Type	Units					Dimension (unit：mm³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

Package Outline Dimensions





单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.70	2.00
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252